







SN54HCT573, SN74HCT573

ZHCSPV3G - JULY 2003 - REVISED JULY 2022

# SNx4HCT573 具有三态输出的八路透明 D 型锁存器

### 1 特性

- 4.5V 至 5.5V 的工作电压范围
- 高电流三态输出直接驱动总线或多达 15 个 LSTTL 负载
- 低功耗,I<sub>CC</sub> 最大值为 80µA
- t<sub>pd</sub> 典型值 = 21ns
- 电压为 5V 时,输出驱动为 ±6mA
- 低输入电流,最大值 1µA
- 输入兼容 TTL 电压
- 总线结构引脚分配

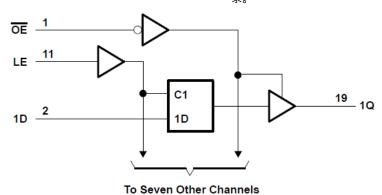
### 2 说明

这些八路透明 D 型锁存器具有专门设计用于驱动高容 性或较低阻抗负载的三态输出。'HCT573 器件尤其适 用于实现缓冲寄存器、I/O 端口、双向总线驱动器和工 作寄存器。

### 器件信息

器件型号	<b>封装</b> <sup>(1)</sup>	封装尺寸 ( 标称值 )
SN74HCT573DW	SOIC (20)	12.80mm × 7.50mm
SN74HCT573DB	SSOP (20)	7.20mm × 5.30mm
SN74HCT573N	PDIP (20)	25.40mm × 6.35mm
SN74HCT573NS	SO (20)	15.00mm × 5.30mm
SN74HCT573PW	TSSOP (20)	6.50mm × 4.40mm

如需了解所有可用封装,请参阅数据表末尾的可订购产品附 录。



功能方框图

English Data Sheet: SCLS176



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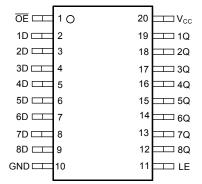
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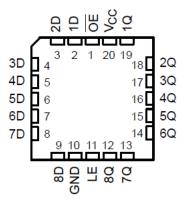
N was 69 is now 84.6, NS was 60 is now 113.4, PW was 83 is now 131.8......4



# **4 Pin Configuration and Functions**



J, W, DB, DW, N, NS, or PW package 20-Pin CDIP, CFP, SSOP, SOIC, PDIP, SO, or TSSOP Top View



FK package 20-Pin LCCC Top View



### **5 Specifications**

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.5	7	V
I <sub>IK</sub>	Input clamp current <sup>(2)</sup>	$(V_I < 0 \text{ or } V_I > V_{CC})$		±20	mA
I <sub>OK</sub>	Output clamp current <sup>(2)</sup>	$(V_O < 0 \text{ or } V_O > V_{CC})$		±20	mA
Io	Continuous output current	(V <sub>O</sub> = 0 to V <sub>CC</sub> )		±35	mA
	Continuous current through Vo	c or GND		±70	mA
T <sub>J</sub>	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## 5.2 Recommended Operating Conditions<sup>(1)</sup>

			SN5	4HCT57	3 <sup>(2)</sup>	SN	SN74HCT573		
			MIN	NOM	MAX	MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage		4.5	5	5.5	4.5	5	5.5	V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2			2			V
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V			0.8			0.8	V
VI	Input voltage	·	0		V <sub>CC</sub>	0		V <sub>CC</sub>	V
Vo	Output voltage		0		V <sub>CC</sub>	0		V <sub>CC</sub>	V
t <sub>t</sub>	Input transition rise/fall time				500			500	ns
T <sub>A</sub>	Operating free-air temperature		- 55		125	- 40		85	°C

<sup>(1)</sup> All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report Implications of Slow or Floating SMOS Inputs, literature number SCBA004.

#### 5.3 Thermal Information

		DW (SOIC)	DB (SSOP)	N (PDIP)	NS (SO)	PW (TSSOP)	
THERMAL	METRIC	20 PINS	20 PINS	20 PINS	20 PINS	20 PINS	UNIT
R <sub>θJA</sub>	Junction-to-ambient thermal resistance <sup>(1)</sup>	109.1	122.7	84.6	113.4	131.8	°C/W
R <sub>θJC (top)</sub>	Junction-to-case (top) thermal resistance	76	81.6	72.5	78.6	72.2	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	77.6	77.5	65.3	78.4	82.8	°C/W
$\Psi_{ m JT}$	Junction-to-top characterization parameter	51.5	46.1	55.3	47.1	21.5	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	77.1	77.1	65.2	78.1	82.4	°C/W
R <sub>0JC (bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC package thermal metrics application report.

<sup>(2)</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>(2)</sup> SN54HCT573 is in product preview.



#### 5.4 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST	V 00	1	Γ <sub>A</sub> = 25°C		SN54HCT	573 <sup>(3)</sup>	SN74HC	T573	UNIT
PARAMETER	CONDITIONS <sup>(1)</sup>	V <sub>CC</sub> (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNII
V <sub>OH</sub>	I <sub>OH</sub> = – 20 μA	4.5	4.4	4.499		4.4		4.4		V
VOH	$I_{OH} = -6 \text{ mA}$	4.5	3.98	4.3		3.7		3.84		v
V <sub>OL</sub>	I <sub>OL</sub> = 20 μA	4.5		0.001	0.1		0.1		0.1	V
VOL	I <sub>OL</sub> = 6 mA	4.5		0.17	0.26		0.4		0.33	v
I <sub>I</sub>	$V_I = V_{CC}$ or 0	5.5		±0.1	±100		±1000		±1000	nA
I <sub>OZ</sub>	$V_O = V_{CC}$ or 0	5.5		±0.01	±0.5		±10		±5	μA
I <sub>CC</sub>	$V_I = V_{CC}$ or 0. $I_O = 0$	5.5			8		160		80	μA
ΔI <sub>CC</sub> <sup>(2)</sup>	One input at 0.5 V or 2.4 V, Other inputs at 0 or V <sub>CC</sub>	5.5		1.4	2.4		3		2.9	mA
C <sub>i</sub>		4.5 to 5.5		3	10		10		10	pF

- 1)  $V_I = V_{IH}$  or  $V_{IL}$ , unless otherwise noted.
- (2) This is the increase in supply current for each input that is at one of the specified TTL voltage levels, rather than 0 V or V<sub>CC</sub>.
- (3) SN54HCT573 is in product preview.

### 5.5 Timing Requirements

		V <sub>cc</sub>	V <sub>CC</sub> T <sub>A</sub> = 25°C		SN54HCT573 <sup>(1)</sup>		SN74HCT573		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
	Pulse duration, LE high	4.5	20		30		25		no
t <sub>W</sub>	Fulse duration, LE nigh	5.5	17		27		23		ns
	Cotun time data before LT	4.5	10		15		13		
t <sub>su</sub>	Setup time, data before LE↓	5.5	9		14		12		ns
	Hold time, data after LE⊥	4.5	5		5		5		no
t <sub>h</sub>	noid tille, data after LE↓	5.5	5		5		5		ns

<sup>(1)</sup> SN54HCT573 is in product preview.

### **5.6 Switching Characteristics**

C<sub>L</sub> = 50 pF. See Figure 6

PARAM	FROM (INPUT)	TO (OUTPUT)	V 00	T <sub>A</sub> = 25°C		SN54HCT57	73 <sup>(1)</sup>	SN74HC	Г573		
ETER	FROW (INFOT)	10 (001701)	V <sub>CC</sub> (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
	D	0	4.5		25	35		53		44	
	t <sub>pd</sub>	Q	5.5		21	32		48		40	ns
'pd	LE	Any Q	4.5		28	35		53		44	115
LL	Any Q	5.5		25	32		48		40		
t <sub>en</sub>	ŌĒ	Any Q	4.5		26	35		53		44	ns
'en	ÖL	Ally Q	5.5		23	32		48		40	113
t	ŌĒ	Any Q	4.5		23	35		53		44	ns
t <sub>dis</sub>	OL	Ally Q	5.5		22	32		48		40	113
t.		Any Q	4.5		9	12		18		15	ns
t <sub>t</sub>		Aily Q	5.5		9	11		16		14	113

(1) SN54HCT573 is in product preview.



### **5.6 Switching Characteristics**

C<sub>I</sub> = 150 pF. See Figure 6

PARAM	FROM (NPILL)   TO (OTTPILL)			T <sub>A</sub> = 25°C			SN54HC1	573 <sup>(1)</sup>	SN74HCT573		
ETER	FROW (INFOT)	10 (001701)	V <sub>CC</sub> (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
	D	Q	4.5		32	52		79		65	
	D	LE Any Q	5.5		27	47		71		59	no
t <sub>pd</sub>	15		4.5		38	52		79		65	ns
	LC		5.5		36	47		71		59	
+	ŌĒ	Any O	4.5		33	52		79		65	ns
t <sub>en</sub>	OE	Any Q	5.5		28	47		71		59	115
t <sub>t</sub> An	Any O	4.5		18	42		63		53		
		Any Q			16	38		57		48	ns

<sup>(1)</sup> SN54HCT573 is in product preview.

# **5.7 Operating Characteristics**

 $T_A = 25^{\circ}C$ 

		Test Conditions	TYP	UNIT	
C <sub>pd</sub>	Power dissipation capacitance per latch	No load	50	pF	



#### **6 Parameter Measurement Information**

 $t_{pd}$  is the maximum between  $t_{PLH}$  and  $t_{PHL}$ 

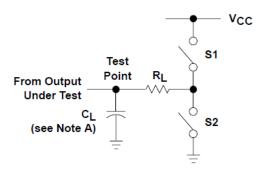


图 6-1. Load Circuit

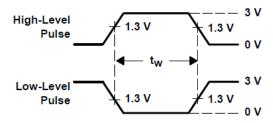


图 6-2. Voltage Waveforms
Pulse Durations

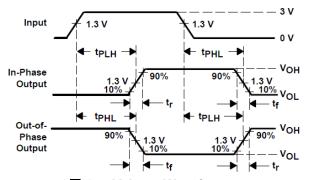
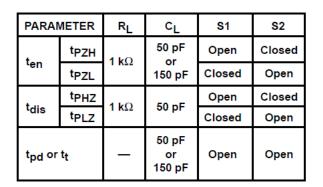


图 6-4. Voltage Waveforms
Propagation Delay and Output Rise and Fall Times



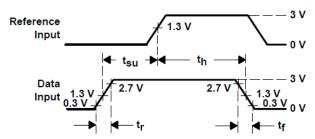


图 6-3. Voltage Waveforms Setup and Hold and Input Rise and Fall Times

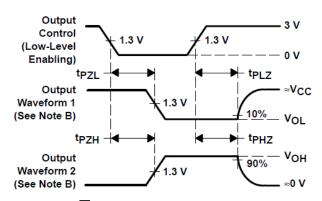


图 6-5. Voltage Waveforms Enable and Diable Times for 3-State Outputs

- A. C<sub>L</sub> includes probe and test-fixture capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when diabled by the output control.
- Waveform 2 is for an output with internal conditions such that the output is high except when diabled by the output control.
- C. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_O = 50 \Omega$ ,  $t_r = 6 \text{ ns}$ ,  $t_f = 6 \text{ ns}$ .
- D. The outputs are measured one at a time with one input transition per measurement.
- E.  $t_{Pl,7}$  and  $t_{PH7}$  are the same as  $t_{dis}$ .
- F.  $t_{PZI}$  and  $t_{PZH}$  are the same as  $t_{en}$ .

### 7 Detailed Description

#### 7.1 Overview

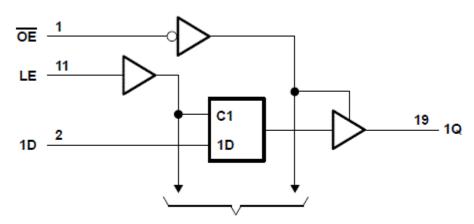
These octal transparent D-type latches feature 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. The 'HCT573 devices are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

While the latch-enable (LE) input is high, the Q outputs respond to the data (D) inputs. When LE is low, the outputs are latched to retain the data that was set up at the D inputs.

A buffered output-enable  $(\overline{OE})$  input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components.

 $\overline{\text{OE}}$  does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

#### 7.2 Functional Block Diagram



To Seven Other Channels

图 7-1. Functional Block Diagram

### 7.3 Device Functional Modes

# Function Table (Each Flip-Flop)

	INPUTS					
ŌĒ	LE	D	Q			
L	Н	Н	Н			
L	Н	L	L			
L	L	X	$Q_0$			
Н	Χ	X	Z			



### 8 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- $\mu$ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

### 9 Layout

#### 9.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.



### 10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

#### **10.1 Documentation Support**

#### 10.1.1 Related Documentation

#### 10.2 接收文档更新通知

要接收文档更新通知,请导航至 ti.com 上的器件产品文件夹。点击*订阅更新* 进行注册,即可每周接收产品信息更 改摘要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

#### 10.3 支持资源

TI E2E™ 支持论坛是工程师的重要参考资料,可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者"按原样"提供。这些内容并不构成 TI 技术规范,并且不一定反映 TI 的观点;请参阅 TI 的《使用条款》。

#### 10.4 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments. 所有商标均为其各自所有者的财产。

#### 10.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 10.6 术语表

#### TI 术语表 本术语表列出并解释了术语、首字母缩略词和定义。

#### 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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#### PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package   Pins	Package qty   Carrier	<b>RoHS</b> (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
SN74HCT573DBR	A ativo	Production	CCOD (DD)   20	2000 11 ADOL TAD	Yes	(4)	(5) Level-1-260C-UNLIM	-40 to 85	HT573
	Active		SSOP (DB)   20	2000   LARGE T&R		NIPDAU   NIPDAU			
SN74HCT573DBR.A	Active	Production	SSOP (DB)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HT573
SN74HCT573DBRG4	Active	Production	SSOP (DB)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HT573
SN74HCT573DW	Obsolete	Production	SOIC (DW)   20	-	-	Call TI	Call TI	-40 to 85	HCT573
SN74HCT573DWR	Active	Production	SOIC (DW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT573
SN74HCT573DWR.A	Active	Production	SOIC (DW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT573
SN74HCT573DWR.B	Active	Production	SOIC (DW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT573
SN74HCT573DWRG4	Active	Production	SOIC (DW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT573
SN74HCT573N	Active	Production	PDIP (N)   20	20   TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	SN74HCT573N
SN74HCT573N.A	Active	Production	PDIP (N)   20	20   TUBE	Yes	NIPDAU	N/A for Pkg Type	-40 to 85	SN74HCT573N
SN74HCT573NSR	Active	Production	SOP (NS)   20	2000   LARGE T&R	Yes	NIPDAU   NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT573
SN74HCT573NSR.A	Active	Production	SOP (NS)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HCT573
SN74HCT573PW	Obsolete	Production	TSSOP (PW)   20	-	-	Call TI	Call TI	-40 to 85	HT573
SN74HCT573PW.B	Obsolete	Production	TSSOP (PW)   20	-	-	Call TI	Call TI	-40 to 85	HT573
SN74HCT573PWR	Active	Production	TSSOP (PW)   20	2000   LARGE T&R	Yes	NIPDAU   NIPDAU	Level-1-260C-UNLIM	-40 to 85	HT573
SN74HCT573PWR.A	Active	Production	TSSOP (PW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HT573
SN74HCT573PWR.B	Active	Production	TSSOP (PW)   20	2000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HT573

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.



# **PACKAGE OPTION ADDENDUM**

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(6) Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

# **PACKAGE MATERIALS INFORMATION**

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCT573DBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN74HCT573DWR	SOIC	DW	20	2000	330.0	24.4	10.9	13.3	2.7	12.0	24.0	Q1
SN74HCT573NSR	SOP	NS	20	2000	330.0	24.4	8.4	13.0	2.5	12.0	24.0	Q1
SN74HCT573PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.0	1.4	8.0	16.0	Q1

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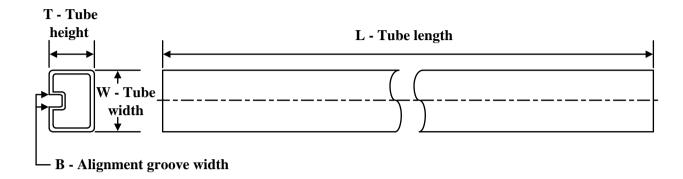
#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCT573DBR	SSOP	DB	20	2000	353.0	353.0	32.0
SN74HCT573DWR	SOIC	DW	20	2000	356.0	356.0	45.0
SN74HCT573NSR	SOP	NS	20	2000	356.0	356.0	45.0
SN74HCT573PWR	TSSOP	PW	20	2000	353.0	353.0	32.0

# **PACKAGE MATERIALS INFORMATION**

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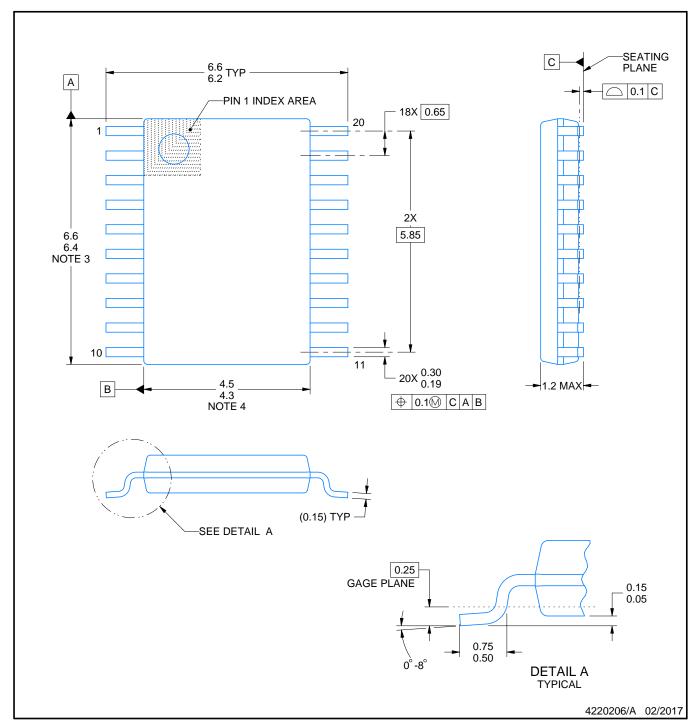
### **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74HCT573N	N	PDIP	20	20	506	13.97	11230	4.32
SN74HCT573N.A	N	PDIP	20	20	506	13.97	11230	4.32



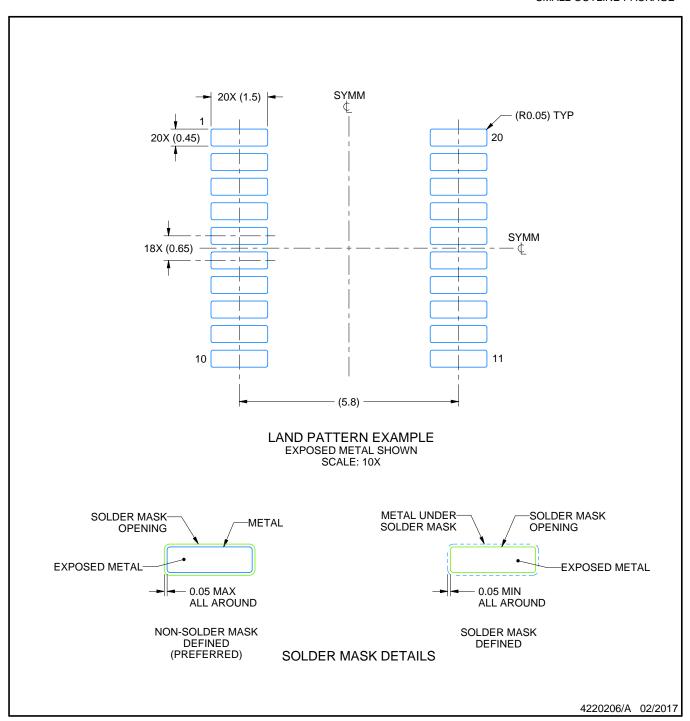


- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



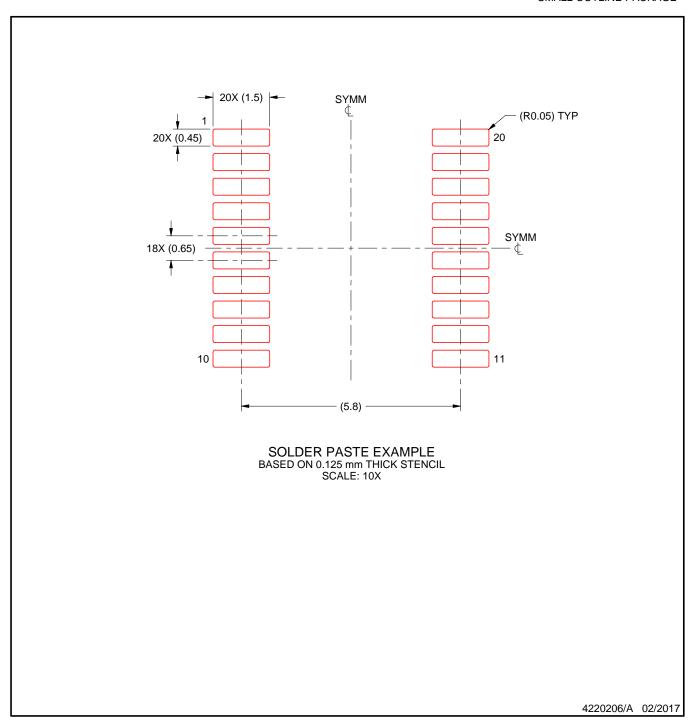


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



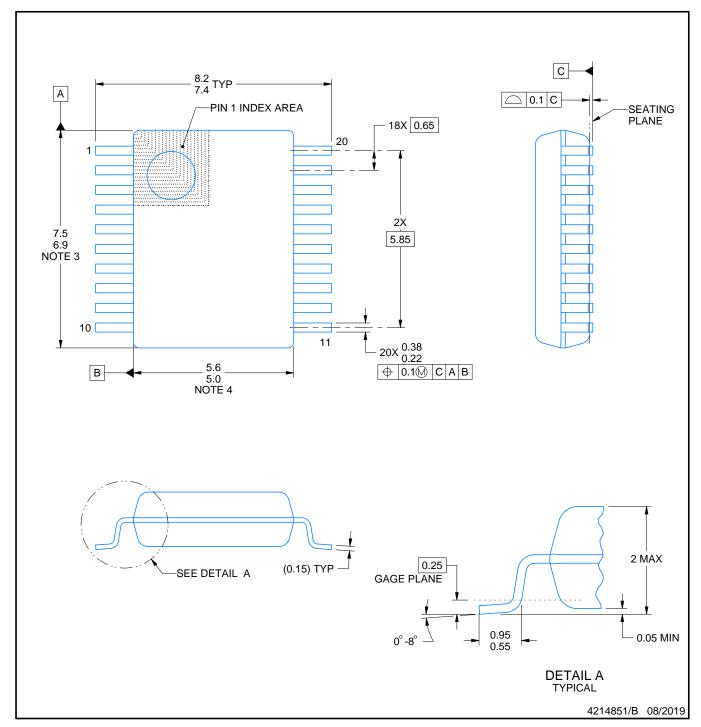


NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





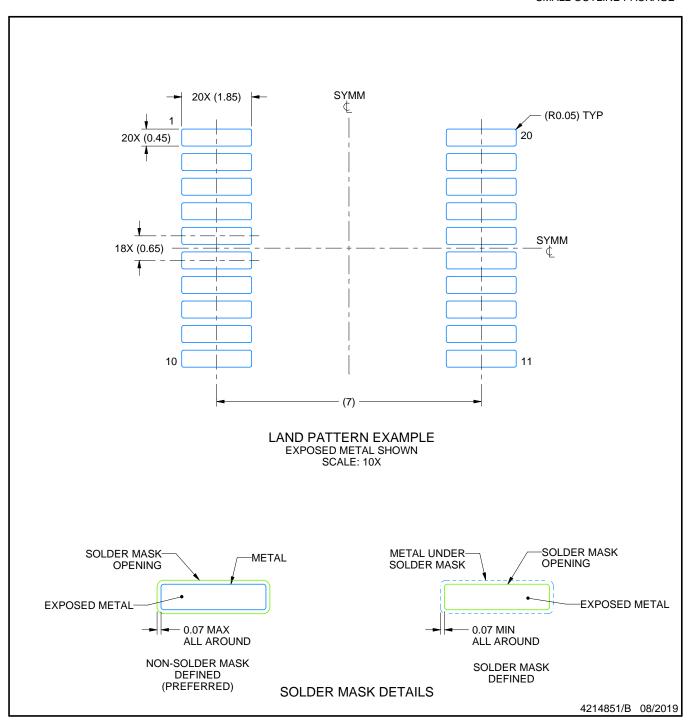


- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.



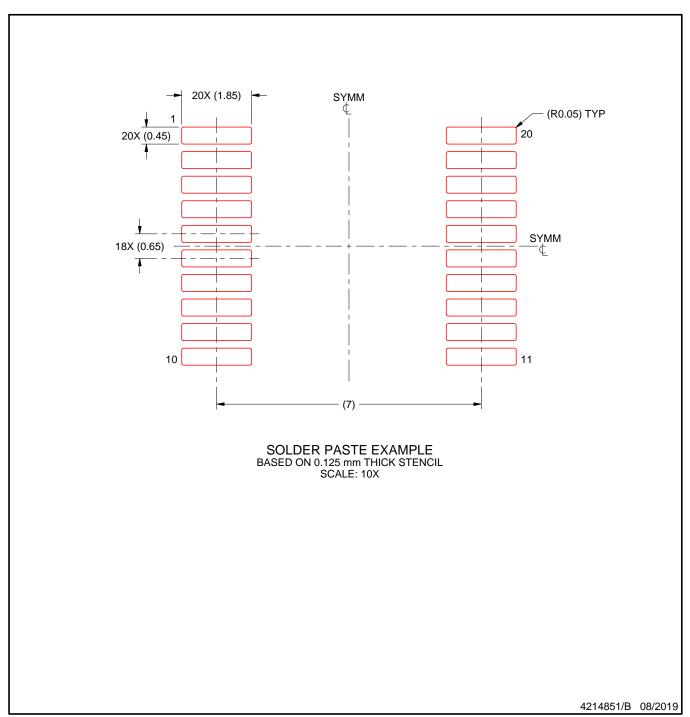


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



### **MECHANICAL DATA**

# NS (R-PDSO-G\*\*)

# 14-PINS SHOWN

### PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



# N (R-PDIP-T\*\*)

# PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.





SOIC



- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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